Yasuo Koide

List of Publications by Year
in descending order

293 papers	10,947 citations	34105 52 h-index	38395 95 g-index
298 all docs	298 docs citations	298 times ranked	9450 citing authors

#	Article	IF	Citations
1	Improvement of structural quality of AlN layers grown on c-plane sapphire substrate by metalâ€“organic vapor phase epitaxy using post-growth annealing with trimethylgallium. AIP Advances, 2022, 12, 015203.	1.3	0
2	Investigation of Ohmic Contact Resistance, Surface Resistance, and Channel Resistance for Hydrogen-Terminated Diamond MOSFETs. IEEE Transactions on Electron Devices, 2022, 69, 1181-1185.	3.0	3
3	Stress effect on the resonance properties of single-crystal diamond cantilever resonators for microscopy applications. Ultramicroscopy, 2022, 234, 113464.	1.9	5
4	Science and Technology of Integrated Super-High Dielectric Constant AlOx/TiOy Nanolaminates / Diamond for MOS Capacitors and MOSFETs. Carbon, 2021, 172, 112-121.	10.3	10
5	Highly-crystalline 6 inch free-standing GaN observed using X-ray diffraction topography. CrystEngComm, 2021, 23, 1628-1633.	2.6	4
6	Interface characteristics of Î²-Ga2O3/Al2O3/Pt capacitors after postmetallization annealing. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, .	2.1	7
7	Suppression of the regrowth interface leakage current in AlGaN/GaN HEMTs by unactivated Mg doped GaN layer. Applied Physics Letters, 2021, 118, 072103.	3.3	5
8	Thermal mismatch induced stress characterization by dynamic resonance based on diamond MEMS. Applied Physics Express, 2021, 14, 045501.	2.4	3
9	Reliable Ohmic Contact Properties for Ni/Hydrogen-Terminated Diamond at Annealing Temperature up to 900 Â°C. Coatings, 2021, 11, 470.	2.6	0
10	Ambient-hydrogen-induced changes in the characteristics of Pt/GaN Schottky diodes fabricated on bulk GaN substrates. Japanese Journal of Applied Physics, 2021, 60, 068003.	1.5	0
11	Temperature dependence of Young's modulus of single-crystal diamond determined by dynamic resonance. Diamond and Related Materials, 2021, 116, 108403.	3.9	17
12	Integrated TbDyFe Film on a Singleâ€Crystal Diamond Microelectromechanical Resonator for Magnetic Sensing. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2100352.	2.4	2
13	The electric double layer effect and its strong suppression at Li+ solid electrolyte/hydrogenated diamond interfaces. Communications Chemistry, 2021, 4, .	4.5	15
14	Boron-Doped Diamond MOSFETs With High Output Current and Extrinsic Transconductance. IEEE Transactions on Electron Devices, 2021, 68, 3963-3967.	3.0	10
15	Influence of HfO2 and SiO2 interfacial layers on the characteristics of n-GaN/HfSiOx capacitors using plasma-enhanced atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, .	2.1	2
16	Polarization-induced hole doping for long-wavelength In-rich InGaN solar cells. Applied Physics Letters, 2021, 119, .	3.3	6
17	Study of HfSiO_x film as gate insulator for GaN power device. , 2021, , .		0
18	Enhanced magnetic sensing performance of diamond MEMS magnetic sensor with boron-doped FeGa film. Carbon, 2020, 170, 294-301.	10.3	18

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19	Fixed charges investigation in Al2O3/hydrogenated-diamond metal-oxide-semiconductor capacitors. Applied Physics Letters, 2020, 117, .	3.3	18
20	Surface potential imaging and characterizations of a GaN p-n junction with Kelvin probe force microscopy. AIP Advances, 2020, 10, .	1.3	7
21	Epitaxial Combination of Two-Dimensional Hexagonal Boron Nitride with Single-Crystalline Diamond Substrate. ACS Applied Materials & Interfaces, 2020, 12, 46466-46475.	8.0	13
22	Thermal stability investigation for Ohmic contact properties of Pt, Au, and Pd electrodes on the same hydrogen-terminated diamond. AIP Advances, 2020, 10, .	1.3	6
23	Effect of Annealing Temperature on Performances of Boron-Doped Diamond Metalâ€“Semiconductor Field-Effect Transistors. IEEE Transactions on Electron Devices, 2020, 67, 1680-1685.	3.0	10
24	Layered boron nitride enabling high-performance AlGaN/GaN high electron mobility transistor. Journal of Alloys and Compounds, 2020, 829, 154542.	5.5	19
25	Surface morphology smoothing of a 2 inch-diameter GaN homoepitaxial layer observed by X-ray diffraction topography. RSC Advances, 2020, 10, 1878-1882.	3.6	3
26	Electrical readout/characterization of single crystal diamond (SCD) cantilever resonators. Diamond and Related Materials, 2020, 103, 107711.	3.9	2
27	Enhancing Delta E Effect at High Temperatures of Galfenol/Ti/Single-Crystal Diamond Resonators for Magnetic Sensing. ACS Applied Materials & Interfaces, 2020, 12, 23155-23164.	8.0	24
28	Coupling of magneto-strictive FeGa film with single-crystal diamond MEMS resonator for high-reliability magnetic sensing at high temperatures. Materials Research Letters, 2020, 8, 180-186.	8.7	19
29	Precise characterization of atomic-scale corrosion of single crystal diamond in H2 plasma based on MEMS/NEMS. Corrosion Science, 2020, 170, 108651.	6.6	6
30	Influence of post-deposition annealing on characteristics of Pt/Al2O3/Î²-Ga2O3 MOS capacitors. Microelectronic Engineering, 2019, 216, 111040.	2.4	20
31	Vertical-Type Ni/GaN UV Photodetectors Fabricated on Free-Standing GaN Substrates. Applied Sciences (Switzerland), 2019, 9, 2895.	2.5	18
32	Anisotropic mosaicity and lattice-plane twisting of an m-plane GaN homoepitaxial layer. CrystEngComm, 2019, 21, 4036-4041.	2.6	5
33	Boosting the doping efficiency of Mg in p-GaN grown on the free-standing GaN substrates. Applied Physics Letters, 2019, 115, .	3.3	22
34	Hydrogen effect on Pt/Al2O3/GaN metal-oxide-semiconductor capacitors. Japanese Journal of Applied Physics, 2019, 58, 100915.	1.5	5
35	High Output Current Boron-Doped Diamond Metal-Semiconductor Field-Effect Transistors. IEEE Electron Device Letters, 2019, 40, 1748-1751.	3.9	17
36	High-k Oxides on Hydrogenated-Diamond for Metal-Oxide-Semiconductor Field-Effect Transistors [Invited]. , 2019, , .		0

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37	Influence of post-deposition annealing on interface characteristics at Al₂O₃/n-GaN. , 2019, , .		3
38	Investigation of Al2O3/GaN interface properties by sub-bandgap photo-assisted capacitance-voltage technique. AIP Advances, 2019, 9, .	1.3	17
39	Single-crystal diamond microelectromechanical resonator integrated with a magneto-strictive galfenol film for magnetic sensing. Carbon, 2019, 152, 788-795.	10.3	26
40	High Current Output Hydrogenated Diamond Triple-Gate MOSFETs. IEEE Journal of the Electron Devices Society, 2019, 7, 561-565.	2.1	3
41	⁷¹Ga NMR characterization of an n-doped free-standing gallium nitride wafer. Japanese Journal of Applied Physics, 2019, 58, 031003.	1.5	0
42	Operations of hydrogenated diamond metalâ€“oxideâ€“semiconductor field-effect transistors after annealing at 500 Â°C. Journal Physics D: Applied Physics, 2019, 52, 315104.	2.8	13
43	Lattice-plane bending angle modulation of Mg-doped GaN homoepitaxial layer observed by X-ray diffraction topography. CrystEngComm, 2019, 21, 2281-2285.	2.6	4
44	Energyâ€Efficient Metalâ€“Insulatorâ€“Metalâ€Semiconductor Fieldâ€Effect Transistors Based on 2D Carrier Gases. Advanced Electronic Materials, 2019, 5, 1800832.	5.1	39
45	Mapping of a Lattice-Plane Tilting in a <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mrow><mml:mi>Ga</mml:mi><mml:mi mathvariant="normal">N</mml:mi></mml:mrow></mml:math> Wafer Using Energy-Resolved X-Ray Diffraction Topography. Physical Review Applied, 2019, 11, .	3.8	5
46	Single Crystal Diamond Micromechanical and Nanomechanical Resonators. Topics in Applied Physics, 2019, , 91-121.	0.8	2
47	(Invited) Characteristics of Several High-k Gate Insulators for GaN Power Device. ECS Transactions, 2019, 92, 109-117.	0.5	2
48	Threshold Voltage Instability of Diamond Metalâ€“Oxideâ€“Semiconductor Fieldâ€Effect Transistors Based on 2D Hole Gas. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1900538.	1.8	2
49	High-quality SiN_x/p-GaN metal-insulator-semiconductor interface with low-density trap states. Journal Physics D: Applied Physics, 2019, 52, 085105.	2.8	9
50	Characteristics of Al₂O₃/native oxide/n-GaN capacitors by post-metallization annealing. Semiconductor Science and Technology, 2019, 34, 034001.	2.0	17
51	Ultrahigh Performance Onâ€Chip Single Crystal Diamond NEMS/MEMS with Electrically Tailored Selfâ€Sensing Enhancing Actuation. Advanced Materials Technologies, 2019, 4, 1800325.	5.8	25
52	High-performance visible to near-infrared photodetectors by using (Cd,Zn)Te single crystal. Optics Express, 2019, 27, 8935.	3.4	14
53	A density functional study of the effect of hydrogen on electronic properties and band discontinuity at anatase TiO2/diamond interface. Journal of Applied Physics, 2018, 123, .	2.5	8
54	Suppression in the electrical hysteresis by using CaF2 dielectric layer for p-GaN MIS capacitors. Journal of Applied Physics, 2018, 123, .	2.5	17

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55	Annealing effects on hydrogenated diamond NOR logic circuits. Applied Physics Letters, 2018, 112, .	3.3	15
56	Synchrotron X-ray diffraction characterization of the inheritance of GaN homoepitaxial thin films grown on selective growth substrates. CrystEngComm, 2018, 20, 2861-2867.	2.6	8
57	Surface and bulk electronic structures of unintentionally and Mg-doped In0.7Ga0.3N epilayer by hard X-ray photoelectron spectroscopy. Journal of Applied Physics, 2018, 123, 095701.	2.5	1
58	Characterization of a 4-inch GaN wafer by X-ray diffraction topography. CrystEngComm, 2018, 20, 7761-7765.	2.6	11
59	Comparative Analysis of Defects in Mg-Implanted and Mg-Doped GaN Layers on Freestanding GaN Substrates. Nanoscale Research Letters, 2018, 13, 403.	5.7	21
60	Investigation of intermediate layers in oxides/GaN(0001) by electron microscopy. Japanese Journal of Applied Physics, 2018, 57, 118003.	1.5	5
61	An Overview of High-k Oxides on Hydrogenated-Diamond for Metal-Oxide-Semiconductor Capacitors and Field-Effect Transistors. Sensors, 2018, 18, 1813.	3.8	12
62	Evaluation of lattice curvature and crystalline homogeneity for 2-inch GaN homo-epitaxial layer. AIP Advances, 2018, 8, .	1.3	5
63	Lattice-plane orientation mapping of homo-epitaxial GaN(0001) thin films via grazing-incidence X-ray diffraction topography in 2-in. wafer. Applied Physics Express, 2018, 11, 081002.	2.4	11
64	Interface trap characterization of Al2O3/GaN vertical-type MOS capacitors on GaN substrate with surface treatments. Journal of Alloys and Compounds, 2018, 767, 600-605.	5.5	26
65	Electron microscopy and ultraviolet photoemission spectroscopy studies of native oxides on GaN(0001). Japanese Journal of Applied Physics, 2018, 57, 098003.	1.5	8
66	Effect of Boron Incorporation on Structural and Optical Properties of AlN Layers Grown by Metalâ€Organic Vapor Phase Epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1800282.	1.8	15
67	Reducing intrinsic energy dissipation in diamond-on-diamond mechanical resonators toward one million quality factor. Physical Review Materials, 2018, 2, .	2.4	17
68	Displacement current of Au/p-diamond Schottky contacts. Materials Science in Semiconductor Processing, 2017, 70, 207-212.	4.0	1
69	Effect of off-cut angle of hydrogen-terminated diamond(111) substrate on the quality of AlN towards high-density AlN/diamond(111) interface hole channel. Journal of Applied Physics, 2017, 121, .	2.5	16
70	Nearly ideal vertical GaN Schottky barrier diodes with ultralow turn-on voltage and on-resistance. Applied Physics Express, 2017, 10, 051001.	2.4	36
71	Enhancement-mode hydrogenated diamond metal-oxide-semiconductor field-effect transistors with Y2O3 oxide insulator grown by electron beam evaporator. Applied Physics Letters, 2017, 110, .	3.3	64
72	Logic Circuits With Hydrogenated Diamond Field-Effect Transistors. IEEE Electron Device Letters, 2017, 38, 922-925.	3.9	49

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73	Deposition of TiO2/Al2O3 bilayer on hydrogenated diamond for electronic devices: Capacitors, field-effect transistors, and logic inverters. Journal of Applied Physics, 2017, 121, .	2.5	42
74	Surface and bulk electronic structures of heavily Mg-doped InN epilayer by hard X-ray photoelectron spectroscopy. Journal of Applied Physics, 2017, 121, .	2.5	5
75	Fabrication of Hydrogenated Diamond Metalâ€“Insulatorâ€“Semiconductor Field-Effect Transistors. Methods in Molecular Biology, 2017, 1572, 217-232.	0.9	5
76	Homoepitaxial diamond chemical vapor deposition for ultra-light doping. Materials Science in Semiconductor Processing, 2017, 70, 197-202.	4.0	8
77	Electron microscopy studies of the intermediate layers at the SiO₂/GaN interface. Japanese Journal of Applied Physics, 2017, 56, 110312.	1.5	28
78	Effect of Sputter Deposition Atmosphere of AlN on the Electrical Properties of Hydrogenâ€Terminated Diamond Field Effect Transistor with AlN/Al₂O₃ Stack Gate. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1700463.	1.8	1
79	Reducing energy dissipation and surface effect of diamond nanoelectromechanical resonators by annealing in oxygen ambient. Carbon, 2017, 124, 281-287.	10.3	11
80	Initial leakage current paths in the vertical-type GaN-on-GaN Schottky barrier diodes. Applied Physics Letters, 2017, 111, .	3.3	55
81	Magnetic Control of Magneto-Electrochemical Cell and Electric Double Layer Transistor. Scientific Reports, 2017, 7, 10534.	3.3	20
82	Low-energy ion scattering spectroscopy and reflection high-energy electron diffraction of native oxides on GaN(0001). Japanese Journal of Applied Physics, 2017, 56, 128004.	1.5	16
83	Improvement of the quality factor of single crystal diamond mechanical resonators. Japanese Journal of Applied Physics, 2017, 56, 024101.	1.5	26
84	Nanometer-thin ALD-Al₂O₃for the improvement of the structural quality of AlN grown on sapphire substrate by MOVPE. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600727.	1.8	5
85	Formation Mechanism and Elimination of Smallâ€Angle Grain Boundary in AlN Grown on (0001) Sapphire Substrate. , 2017, , .		0
86	Mechanism of reverse current increase of vertical-type diamond Schottky diodes. Journal of Applied Physics, 2017, 122, .	2.5	23
87	Crystalline Diamond Substrates for Power Devices. Journal of the Institute of Electrical Engineers of Japan, 2017, 137, 689-692.	0.0	0
88	An Interface Engineered Multicolor Photodetector Based on nâ€Si(111)/TiO₂ Nanorod Array Heterojunction. Advanced Functional Materials, 2016, 26, 1400-1410.	14.9	64
89	Structural properties and transfer characteristics of sputter deposition AlN and atomic layer deposition Al2O3 bilayer gate materials for H-terminated diamond field effect transistors. Journal of Applied Physics, 2016, 120, .	2.5	22
90	Investigation on the interfacial chemical state and band alignment for the sputtering-deposited CaF2/p-GaN heterojunction by angle-resolved X-ray photoelectron spectroscopy. Journal of Applied Physics, 2016, 120, .	2.5	7

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91	Assembly of a high-dielectric constant thin TiOx layer directly on H-terminated semiconductor diamond. Applied Physics Letters, 2016, 108, .	3.3	26
92	High-k ZrO2/Al2O3 bilayer on hydrogenated diamond: Band configuration, breakdown field, and electrical properties of field-effect transistors. Journal of Applied Physics, 2016, 120, .	2.5	25
93	Electrical hysteresis in p-GaN metalâ€“oxideâ€“semiconductor capacitor with atomic-layer-deposited Al₂O₃ as gate dielectric. Applied Physics Express, 2016, 9, 121002.	2.4	19
94	P-Channel InGaN/GaN heterostructure metal-oxide-semiconductor field effect transistor based on polarization-induced two-dimensional hole gas. Scientific Reports, 2016, 6, 23683.	3.3	37
95	Self-assembling diacetylene molecules on atomically flat insulators. Physical Chemistry Chemical Physics, 2016, 18, 31600-31605.	2.8	8
96	Design and fabrication of high-performance diamond triple-gate field-effect transistors. Scientific Reports, 2016, 6, 34757.	3.3	37
97	Optical Filters Based on Nano-Sized Hole and Slit Patterns in Aluminum Films. IEICE Transactions on Electronics, 2016, E99.C, 358-364.	0.6	1
98	Control of normally on/off characteristics in hydrogenated diamond metal-insulator-semiconductor field-effect transistors. Journal of Applied Physics, 2015, 118, .	2.5	35
99	Influence of surface structure of (0001) sapphire substrate on the elimination of small-angle grain boundary in AlN epilayer. AIP Advances, 2015, 5, 097143.	1.3	4
100	Homoepitaxial diamond film growth: High purity, high crystalline quality, isotopic enrichment, and single color center formation. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 2365-2384.	1.8	68
101	InGaN-based thin film solar cells: Epitaxy, structural design, and photovoltaic properties. Journal of Applied Physics, 2015, 117, .	2.5	26
102	Impedance analysis of Al2O3/H-terminated diamond metal-oxide-semiconductor structures. Applied Physics Letters, 2015, 106, 083506.	3.3	16
103	Electrical properties of atomic layer deposited HfO2/Al2O3 multilayer on diamond. Diamond and Related Materials, 2015, 54, 55-58.	3.9	21
104	Energy dissipation in micron- and submicron-thick single crystal diamond mechanical resonators. Applied Physics Letters, 2014, 105, .	3.3	26
105	Diamond FETs using heterojunction and high-k dielectrics. , 2014, , .		0
106	Diamond field effect transistors with a high-dielectric constant Ta₂O₅as gate material. Journal Physics D: Applied Physics, 2014, 47, 245102.	2.8	31
107	A Multilevel Intermediateâ€Band Solar Cell by InGaN/GaN Quantum Dots with a Strainâ€Modulated Structure. Advanced Materials, 2014, 26, 1414-1420.	21.0	40
108	Thermal stabilization and deterioration of the WC/pâ€type diamond (100) Schottkyâ€barrier interface. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 2363-2366.	1.8	11

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109	Diamond Schottky diodes with ideality factors close to 1. Applied Physics Letters, 2014, 105, 133515.	3.3	19
110	Diamond logic inverter with enhancement-mode metal-insulator-semiconductor field effect transistor. Applied Physics Letters, 2014, 105, .	3.3	29
111	Direct observation of the leakage current in epitaxial diamond Schottky barrier devices by conductive-probe atomic force microscopy and Raman imaging. Journal Physics D: Applied Physics, 2014, 47, 355102.	2.8	11
112	Flexible Ultraviolet Photodetectors with Broad Photoresponse Based on Branched ZnSâ€ZnO Heterostructure Nanofilms. Advanced Materials, 2014, 26, 3088-3093.	21.0	251
113	Spectrally dependent photovoltages in Schottky photodiode based on (100) B-doped diamond. Journal of Applied Physics, 2014, 115, 053105.	2.5	12
114	Doping and interface of homoepitaxial diamond for electronic applications. MRS Bulletin, 2014, 39, 499-503.	3.5	49
115	Schottky barrier height and thermal stability of p-diamond (100) Schottky interfaces. Thin Solid Films, 2014, 557, 241-248.	1.8	20
116	Photodetectors: Flexible Ultraviolet Photodetectors with Broad Photoresponse Based on Branched ZnS-ZnO Heterostructure Nanofilms (Adv. Mater. 19/2014). Advanced Materials, 2014, 26, 3087-3087.	21.0	1
117	Low on-resistance diamond field effect transistor with high-k ZrO2 as dielectric. Scientific Reports, 2014, 4, 6395.	3.3	107
118	Interfacial electronic band alignment of Ta2O5/hydrogen-terminated diamond heterojunction determined by X-ray photoelectron spectroscopy. Diamond and Related Materials, 2013, 38, 24-27.	3.9	11
119	Electrical characteristics of hydrogen-terminated diamond metal-oxide-semiconductor with atomic layer deposited HfO2 as gate dielectric. Applied Physics Letters, 2013, 102, .	3.3	42
120	Effective Use of Source Gas for Diamond Growth with Isotopic Enrichment. Applied Physics Express, 2013, 6, 055601.	2.4	24
121	Arbitrary Multicolor Photodetection by Hetero-integrated Semiconductor Nanostructures. Scientific Reports, 2013, 3, 2368.	3.3	41
122	High-detectivity nanowire photodetectors governed by bulk photocurrent dynamics with thermally stable carbide contacts. Nanotechnology, 2013, 24, 495701.	2.6	18
123	Interfacial band configuration and electrical properties of LaAlO3/Al2O3/hydrogenated-diamond metal-oxide-semiconductor field effect transistors. Journal of Applied Physics, 2013, 114, .	2.5	60
124	Impact of Mg concentration on energy-band-depth profile of Mg-doped InN epilayers analyzed by hard X-ray photoelectron spectroscopy. Applied Physics Letters, 2013, 103, .	3.3	8
125	Systematic investigation of surface and bulk electronic structure of undoped In-polar InN epilayers by hard X-ray photoelectron spectroscopy. Journal of Applied Physics, 2013, 114, .	2.5	17
126	Normally-off HfO2-gated diamond field effect transistors. Applied Physics Letters, 2013, 103, .	3.3	105

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127	Temperature and Light Intensity Dependence of Photocurrent Transport Mechanisms in InGaN pâ€“iâ€“n Homojunction Solar Cells. Japanese Journal of Applied Physics, 2013, 52, 08JF04.	1.5	8
128	Analysis of Broken Symmetry in Convergent-Beam Electron Diffraction along <112Ì„0 > and <11Ì„00 > Zone-Axes of AlN for Polarity Determination. Japanese Journal of Applied Physics, 2013, 52, 08JE15.	1.5	5
129	Interfacial chemical bonding state and band alignment of CaF2/hydrogen-terminated diamond heterojunction. Journal of Applied Physics, 2013, 113, 123706.	2.5	7
130	Development of Diamond-based Optical and Electronic Devices. Journal of Smart Processing, 2013, 2, 224-229.	0.1	0
131	Integration of high-dielectric constant Ta2O5 oxides on diamond for power devices. Applied Physics Letters, 2012, 101, .	3.3	41
132	Chemical Vapor Deposition of ¹²C Isotopically Enriched Polycrystalline Diamond. Japanese Journal of Applied Physics, 2012, 51, 090104.	1.5	13
133	Comprehensive Investigation of Single Crystal Diamond Deep-Ultraviolet Detectors. Japanese Journal of Applied Physics, 2012, 51, 090115.	1.5	43
134	Polarization Filters for Visible Light Consisting of Subwavelength Slits in an Aluminum Film. Journal of Lightwave Technology, 2012, 30, 3463-3467.	4.6	9
135	Color Filter Based on Surface Plasmon Resonance Utilizing Sub-Micron Periodic Hole Array in Aluminum Thin Film. IEICE Transactions on Electronics, 2012, E95-C, 251-254.	0.6	5
136	Band offsets of Al2O3 and HfO2 oxides deposited by atomic layer deposition technique on hydrogenated diamond. Applied Physics Letters, 2012, 101, .	3.3	76
137	Nanoelectromechanical switch fabricated from single crystal diamond: Experiments and modeling. Diamond and Related Materials, 2012, 24, 69-73.	3.9	13
138	Development of AlN/diamond heterojunction field effect transistors. Diamond and Related Materials, 2012, 24, 206-209.	3.9	31
139	Controlled formation of wrinkled diamond-like carbon (DLC) film on grooved poly(dimethylsiloxane) substrate. Diamond and Related Materials, 2012, 22, 48-51.	3.9	21
140	Amorphous silicon diamond based heterojunctions with high rectification ratio. Journal of Non-Crystalline Solids, 2012, 358, 2110-2113.	3.1	12
141	Low contact resistance metals for graphene based devices. Diamond and Related Materials, 2012, 24, 171-174.	3.9	94
142	Localized mid-gap-states limited reverse current of diamond Schottky diodes. Journal of Applied Physics, 2012, 111, 104503.	2.5	12
143	InGaN photodiodes using CaF2 insulator for high-temperature UV detection. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 953-956.	0.8	2
144	Comprehensive Investigation of Single Crystal Diamond Deep-Ultraviolet Detectors. Japanese Journal of Applied Physics, 2012, 51, 090115.	1.5	60

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145	Nanophotonics Based on Semiconductor-Photonic Crystal/Quantum Dot and Metal-/Semiconductor-Plasmonics. IEICE Transactions on Electronics, 2012, E95-C, 178-187.	0.6	0
146	Deep-ultraviolet solar-blind photoconductivity of individual gallium oxide nanobelts. Nanoscale, 2011, 3, 1120.	5.6	210
147	WO3 nanowires on carbon papers: electronic transport, improved ultraviolet-light photodetectors and excellent field emitters. Journal of Materials Chemistry, 2011, 21, 6525.	6.7	103
148	Enhanced performance of InGaN solar cell by using a super-thin AlN interlayer. Applied Physics Letters, 2011, 99, .	3.3	62
149	Carbon-Based Materials: Growth, Properties, MEMS/NEMS Technologies, and MEM/NEM Switches. Critical Reviews in Solid State and Materials Sciences, 2011, 36, 66-101.	12.3	55
150	Polarization independent visible color filter comprising an aluminum film with surface-plasmon enhanced transmission through a subwavelength array of holes. Applied Physics Letters, 2011, 98, .	3.3	208
151	Non-destructive detection of killer defects of diamond Schottky barrier diodes. Journal of Applied Physics, 2011, 110, .	2.5	44
152	High-temperature ultraviolet detection based on InGaN Schottky photodiodes. Applied Physics Letters, 2011, 99, .	3.3	61
153	Demonstration of diamond field effect transistors by AlN/diamond heterostructure. Physica Status Solidi - Rapid Research Letters, 2011, 5, 125-127.	2.4	39
154	Nanoelectromechanical switches based on diamond-on-diamond. , 2011, , .		0
155	Bridging wide bandgap nanowires for ultraviolet light detection. , 2011, , .		0
156	Sb2O3nanobelt networks for excellent visible-light-range photodetectors. Nanotechnology, 2011, 22, 165704.	2.6	29
157	High-performance metal-semiconductor-metal InGaN photodetectors using CaF2 as the insulator. Applied Physics Letters, 2011, 98, 103502.	3.3	56
158	An Efficient Way to Assemble ZnS Nanobelts as Ultravioletâ€Light Sensors with Enhanced Photocurrent and Stability. Advanced Functional Materials, 2010, 20, 500-508.	14.9	222
159	Efficient Assembly of Bridged Î²â€Ga₂O₃ Nanowires for Solarâ€Blind Photodetection. Advanced Functional Materials, 2010, 20, 3972-3978.	14.9	292
160	Centimeterâ€Long V₂O₅ Nanowires: From Synthesis to Fieldâ€Emission, Electrochemical, Electrical Transport, and Photoconductive Properties. Advanced Materials, 2010, 22, 2547-2552.	21.0	359
161	Singleâ€Crystalline CdS Nanobelts for Excellent Fieldâ€Emitters and Ultrahigh Quantumâ€Efficiency Photodetectors. Advanced Materials, 2010, 22, 3161-3165.	21.0	342
162	Electrical Transport and Highâ€Performance Photoconductivity in Individual ZrS₂ Nanobelts. Advanced Materials, 2010, 22, 4151-4156.	21.0	169

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163	Singleâ€Crystalline Sb₂Se₃ Nanowires for Highâ€Performance Field Emitters and Photodetectors. Advanced Materials, 2010, 22, 4530-4533.	21.0	147
164	Ultrahighâ€Performance Solarâ€Blind Photodetectors Based on Individual Singleâ€crystalline In₂Ge₂O₇ Nanobelts. Advanced Materials, 2010, 22, 5145-5149.	21.0	249
165	Suspended Singleâ€Crystal Diamond Nanowires for Highâ€Performance Nanoelectromechanical Switches. Advanced Materials, 2010, 22, 5393-5397.	21.0	101
166	Growth mechanism of c-axis-oriented AlN on (1 1 1) diamond substrates by metal-organic vapor phase epitaxy. Journal of Crystal Growth, 2010, 312, 1325-1328.	1.5	23
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